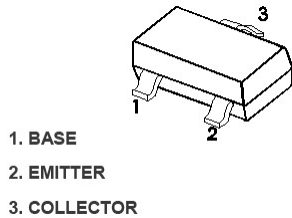


S9014 TRANSISTOR(NPN)

Rev.1.0

SOT-23

SOT-23 贴片塑封三极管 SOT-23 Plastic-Encapsulate Transistors



Marking: J6

特征 Features

- 与 S9015 配对; Complementary to S9015
- 最大功率耗散 200mW; Power Dissipation of 200mW
- 高稳定性和可靠性。High Stability and High Reliability

机械数据 Mechanical Data

- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0
- 安装位置: 任意 Mounting Position: Any

极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current-Continuous	I _C	100	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	625	°C/W

电特性 (TA = 25°C 除非另有规定)

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

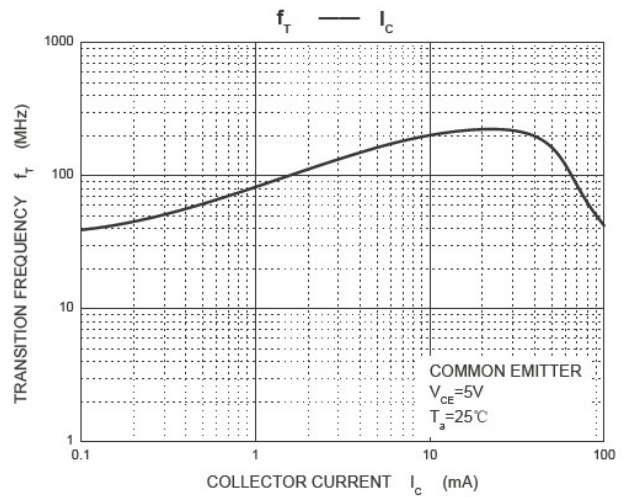
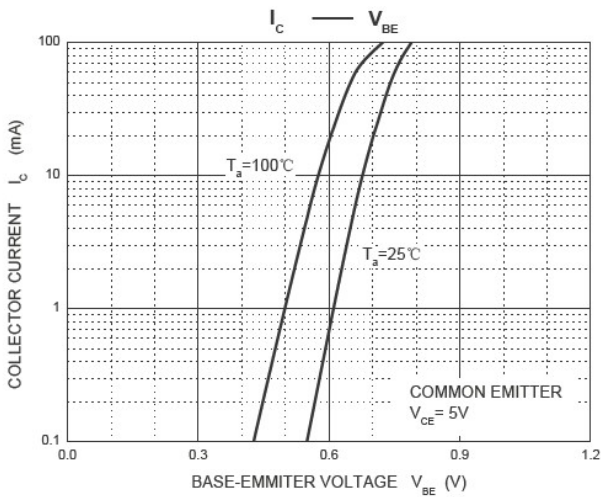
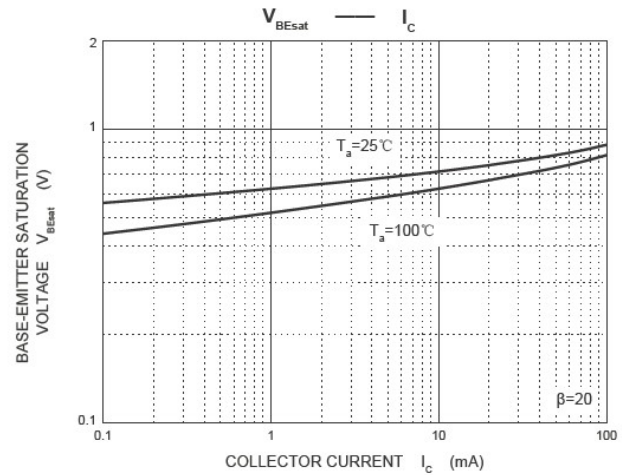
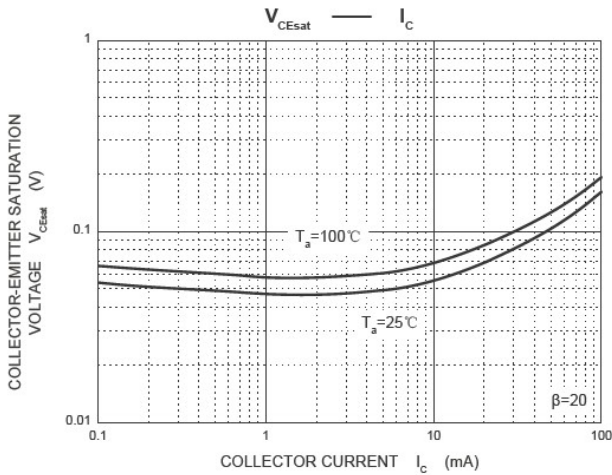
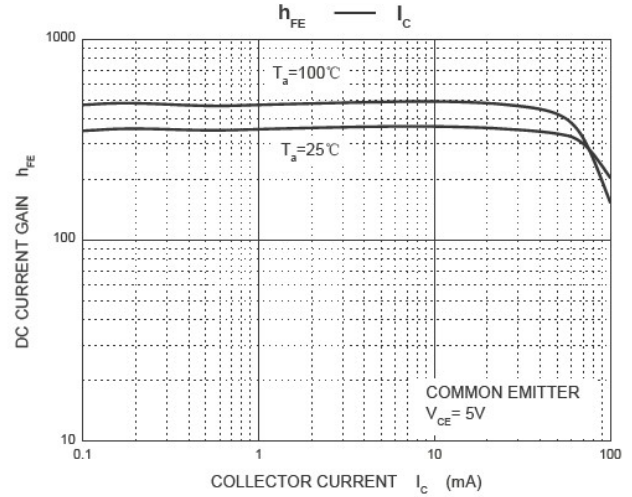
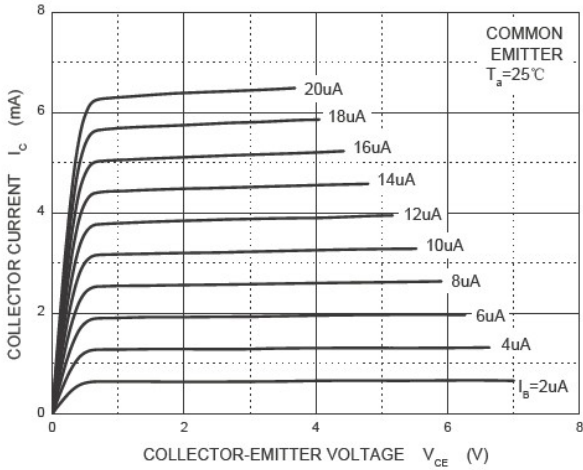
参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =100uA, I _E =0	50		V
Collector-emitter breakdown voltage	V(BR)CEO	I _C =0.1mA, I _B =0	45		V
Emitter-base breakdown voltage	V(BR)EBO	I _E =100uA, I _C =0	5		V
Collector cut-off current	I _{CEO}	V _{CE} =35V, I _B =0		100	nA
Collector cut-off current	I _{CBO}	V _{CB} =50V, I _E =0		100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =3V, I _C =0		100	nA
DC current gain	h _{FE}	V _{CE} =5V, I _C =1mA	200	1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =5mA		0.30	V
Base -emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =5mA		1.00	V
Transition frequency	f _t	V _{CE} =5V, I _C =10mA, f=30MHz	150		MHz

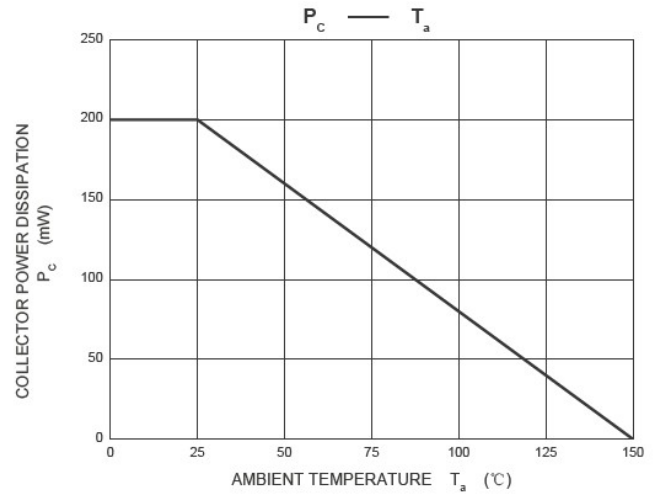
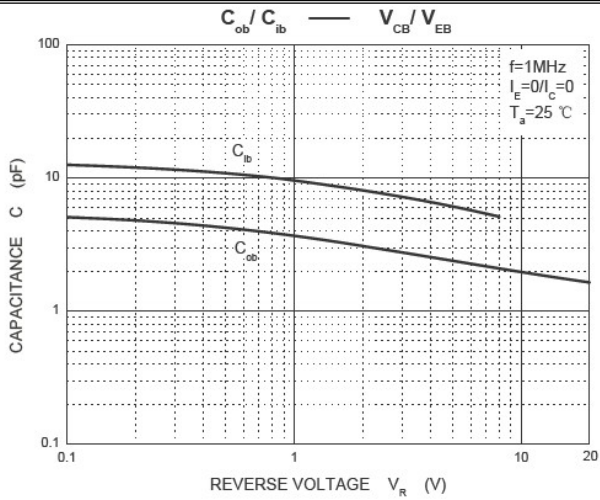
CLASSIFICATION OF h_{FE(1)}

RANK	L	H
RANGE	200-450	450-1000

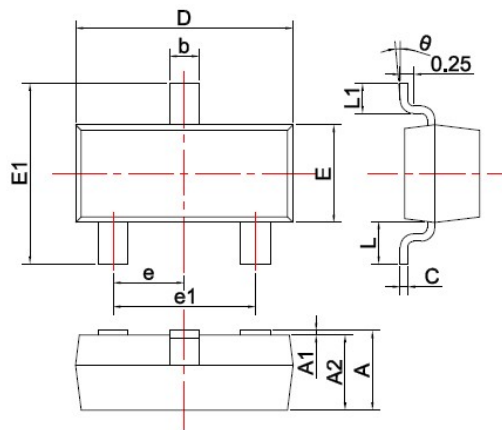
Typical characteristics

Static Characteristic





SOT-23 PACKAGE OUTLINE Plastic surface mounted package

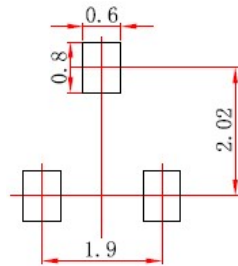


SYMBOL	DIMENSIONS	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

Unit: mm

焊盘设计参考 Precautions: PCB Design

Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [SINEDEVICE manufacturer](#):

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-TL-E](#) [BC856BW-13-F](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [MCH6102-TL-E](#) [BC846B-13-F](#) [2N3879](#) [30A02MH-TL-E](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANSR2N2907AUB](#) [CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#) [MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#) [2N6678](#) [2N2907Ae4](#)